

# HiPerFET™ Power MOSFETs

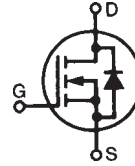
## IXFH36N55Q2

$V_{DSS} = 550 \text{ V}$   
 $I_{D25} = 36 \text{ A}$   
 $R_{DS(on)} = 0.18 \text{ } \Omega$

N-Channel Enhancement Mode  
 Avalanche Rated, Low  $Q_g$   
 Low  $R_g$ , High dv/dt, Low  $t_{rr}$

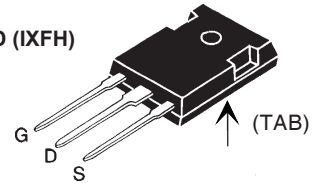
$t_{rr} \leq 250 \text{ ns}$

### Preliminary Data Sheet



Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	550	V
$V_{DGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ ; $R_{GS} = 1 \text{ M}\Omega$	550	V
$V_{GS}$	Continuous	$\pm 30$	V
$V_{GSM}$	Transient	$\pm 40$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$	36	A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , pulse width limited by $T_{JM}$	144	A
$I_{AR}$	$T_C = 25^\circ\text{C}$	36	A
$E_{AR}$	$T_C = 25^\circ\text{C}$	50	mJ
$E_{AS}$	$T_C = 25^\circ\text{C}$	2.5	J
dv/dt	$I_S \leq I_{DM}$ , di/dt $\leq 100 \text{ A}/\mu\text{s}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ\text{C}$ , $R_G = 2 \text{ } \Omega$	20	V/ns
$P_D$	$T_C = 25^\circ\text{C}$	560	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$T_L$	1.6 mm (0.063 in) from case for 10 s	300	$^\circ\text{C}$
$M_d$	Mounting torque	1.13/10 0.9/6	Nm/lb.in. Nm/lb.in.
Weight		6	g

TO-247 AD (IXFH)



G = Gate  
S = Source

TAB = Drain

### Features

- Double metal process for low gate resistance
- International standard packages
- Epoxy meet UL 94 V-0, flammability classification
- Low  $R_{DS(on)}$ , low  $Q_g$
- Avalanche energy and current rated
- Fast intrinsic rectifier

### Applications

- DC-DC converters
- Switched-mode and resonant-mode power supplies, >500kHz switching
- DC choppers
- Pulse generation
- Laser drivers

### Advantages

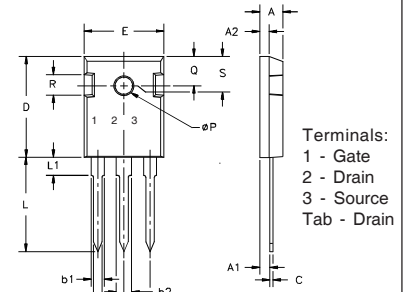
- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$V_{DSS}$	$V_{GS} = 0 \text{ V}$ , $I_D = 250 \text{ } \mu\text{A}$	550		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 4 \text{ mA}$	2.5		5.0 V
$I_{GSS}$	$V_{GS} = \pm 30 \text{ V}_{DC}$ , $V_{DS} = 0$			$\pm 100 \text{ nA}$
$I_{DSS}$	$V_{DS} = V_{DSS}$ , $T_J = 25^\circ\text{C}$ $V_{GS} = 0 \text{ V}$ , $T_J = 125^\circ\text{C}$			25 $\mu\text{A}$ 1 mA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$ , $I_D = 0.5 \cdot I_{D25}$ Pulse test, $t \leq 300 \text{ } \mu\text{s}$ , duty cycle $d \leq 2 \%$			0.18 $\Omega$

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$g_{fs}$	$V_{DS} = 10\text{ V}; I_D = 0.5 \cdot I_{D25}$ , pulse test	15	26	S
$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		4100	pF
$C_{oss}$			660	pF
$C_{rss}$			160	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 2\ \Omega$ (External),		17	ns
$t_r$			13	ns
$t_{d(off)}$			42	ns
$t_f$			8	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		110	nC
$Q_{gs}$			23	nC
$Q_{gd}$			52	nC
$R_{thJC}$			0.22	K/W
$R_{thCK}$		0.25		K/W

Source-Drain Diode		Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
Symbol	Test Conditions	min.	typ.	max.
$I_S$	$V_{GS} = 0\text{ V}$			36 A
$I_{SM}$	Repetitive; pulse width limited by $T_{JM}$			144 A
$V_{SD}$	$I_F = I_S, V_{GS} = 0\text{ V}$ , Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$			1.5 V
$t_{rr}$	$I_F = 25\text{ A} -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$			250 ns
$Q_{RM}$			1	$\mu\text{C}$
$I_{RM}$			9	A

### TO-247 AD (IXFH) Outline



Terminals:  
1 - Gate  
2 - Drain  
3 - Source  
Tab - Drain

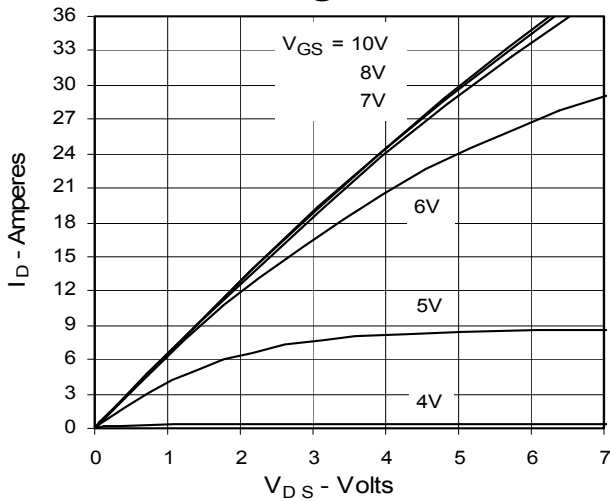
Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A <sub>1</sub>	2.2	2.54	.087	.102
A <sub>2</sub>	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b <sub>1</sub>	1.65	2.13	.065	.084
b <sub>2</sub>	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L <sub>1</sub>		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

IXYS reserves the right to change limits, test conditions, and dimensions.

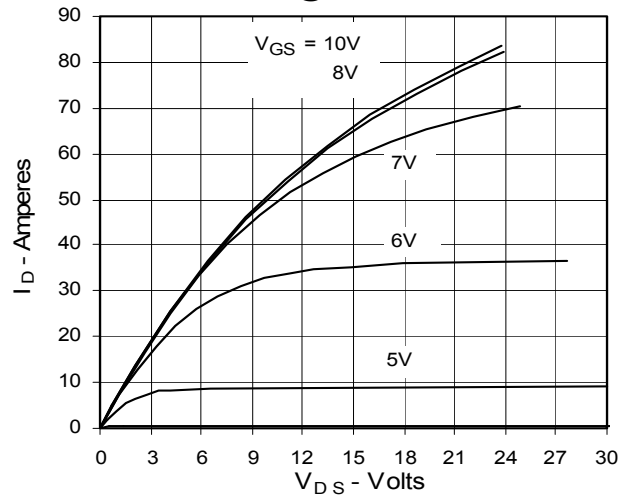
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,850,072	4,931,844	5,034,796	5,063,307	5,237,481	5,381,025	6,404,065B1	6,162,665	6,534,343	6,583,505
4,835,592	4,881,106	5,017,508	5,049,961	5,187,117	5,486,715	6,306,728B1	6,259,123B1	6,306,728B1	6,683,344

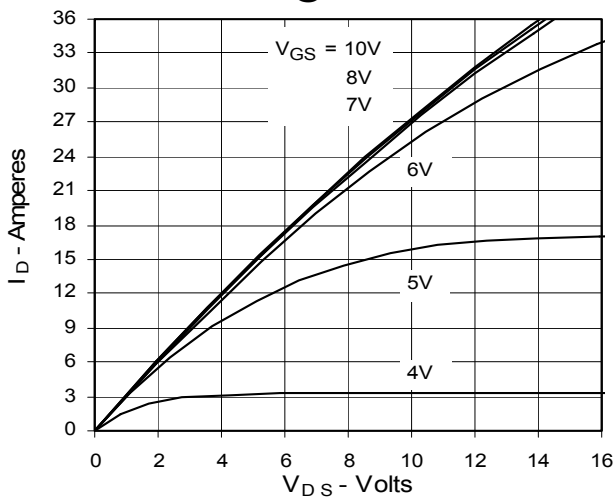
**Fig. 1. Output Characteristics @ 25°C**



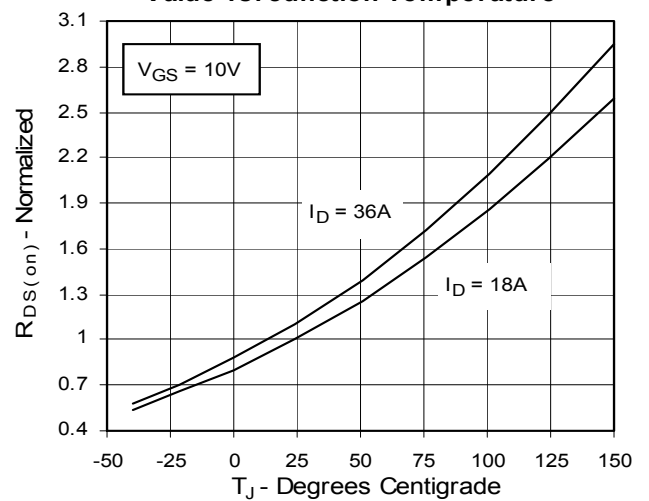
**Fig. 2. Extended Output Characteristics @ 25°C**



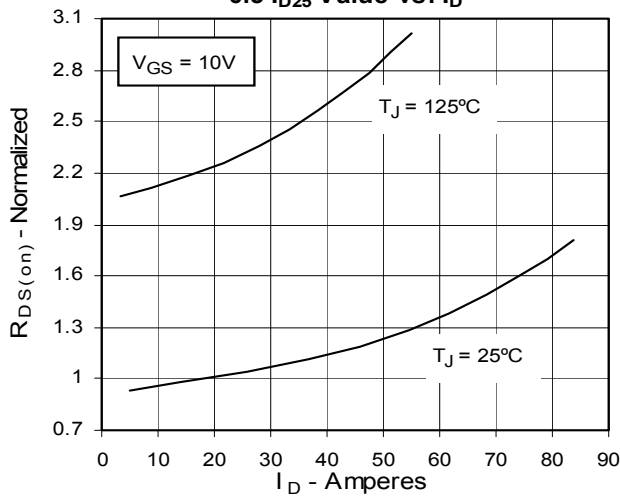
**Fig. 3. Output Characteristics @ 125°C**



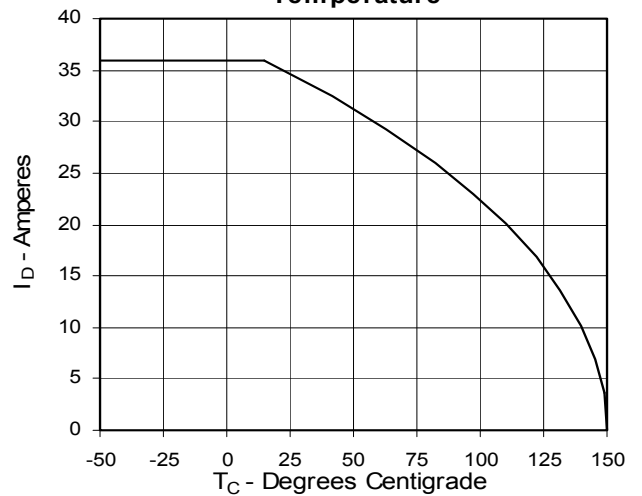
**Fig. 4.  $R_{DS(on)}$  Normalized to 0.5  $I_{D25}$  Value vs. Junction Temperature**



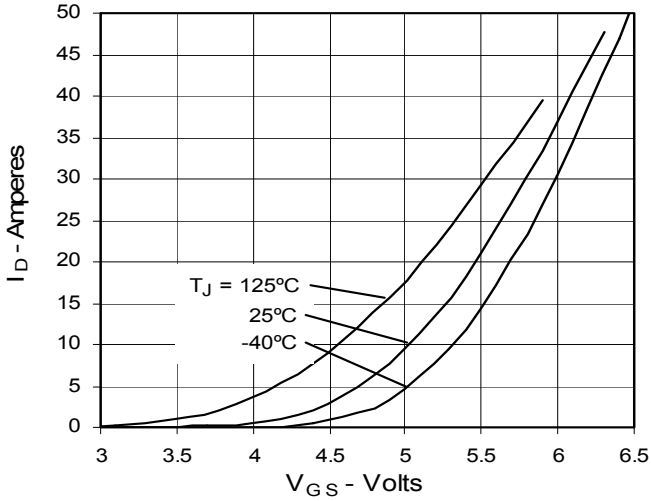
**Fig. 5.  $R_{DS(on)}$  Normalized to 0.5  $I_{D25}$  Value vs.  $I_D$**



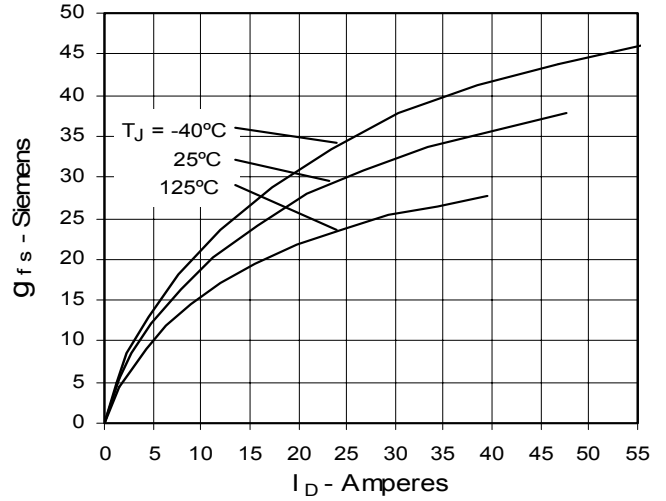
**Fig. 6. Drain Current vs. Case Temperature**



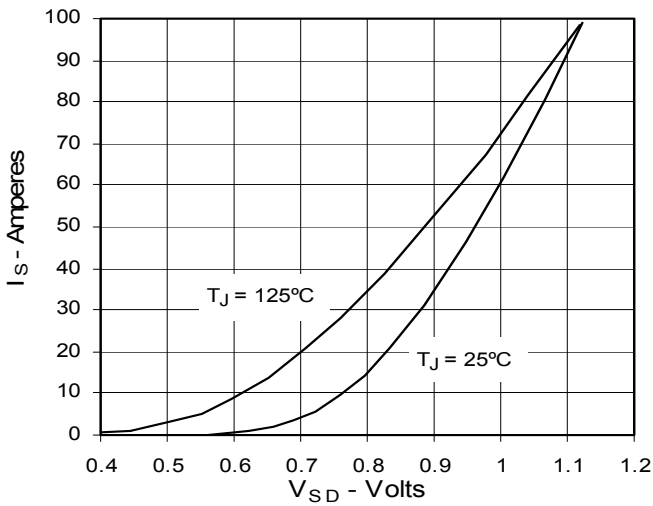
**Fig. 7. Input Admittance**



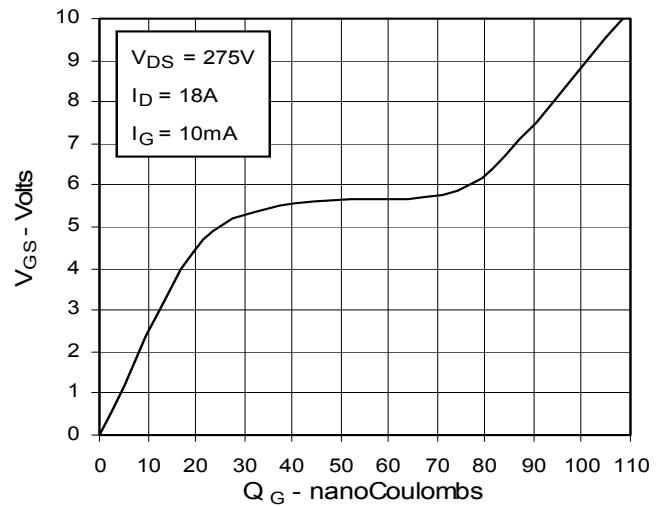
**Fig. 8. Transconductance**



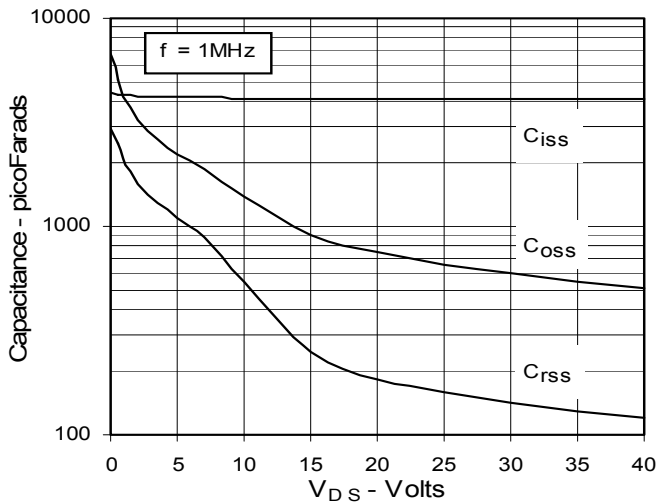
**Fig. 9. Source Current vs. Source-To-Drain Voltage**



**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**



**Fig. 12. Forward-Bias Safe Operating Area**

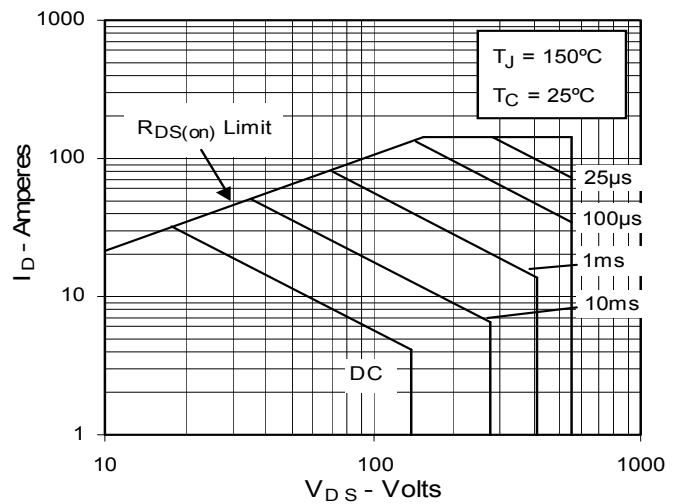


Fig. 13. Maximum Transient Thermal Resistance

